

## IN THE CLAIMS

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1. (previously presented) A solid-state imaging device having an output portion connected to an output end of a horizontal transfer register, the output portion having a gate structure including an oxide film and a nitride film, the solid-state imaging device comprising:

upper layer films allowing ultraviolet rays having a wavelength of 400 nm or less to pass therethrough;

a first metal made shield film formed in such a manner as to cover a region of said gate structure including an oxide film and a nitride film, being disposed above a light receiving portion and a transfer portion, of said solid-state imaging device; and

a second metal made shield film formed in such a manner as to cover a region of said gate structure including the oxide film and the nitride film, entirely shielding at least an output gate or a reset gate of an output portion, of said solid-state imaging device.

2. (previously presented) A solid-state imaging device according to claim 1, wherein said second metal made shield film has an opening at a position directly over a floating diffusion region of said solid-state imaging device.

3. (previously presented) A solid-state imaging device having an output portion connected to an output end of a horizontal transfer register, the output portion having a gate structure including an oxide film and a nitride film, the solid-state imaging device comprising:

upper layer films allowing ultraviolet rays having a wavelength of 400 nm or less to pass therethrough; and

an organic film capable of absorbing said ultraviolet rays, said organic film being formed in such a manner as to cover a region of said gate structure including the oxide film and the nitride film, entirely shielding at least an output gate or a reset gate of an output portion, of said solid-state imaging device.

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